

ABSTRACT OF THE DISCLOSURE

With respect to a liquid phase growth method for a silicon crystal in which the silicon crystal is grown on a substrate by immersing the substrate in a solvent or allowing the substrate to contact the solvent, a gas containing a raw material and/or a dopant is supplied to the solvent after at least a part of the gas is decomposed by application of energy thereto. In this manner, a liquid phase growth method for a silicon crystal, the method capable of achieving continuous growth and suitable for mass production, a manufacturing method for a solar cell and a liquid phase growth apparatus for a silicon crystal are provided.